



# Seminarankündigung

**Dienstag, 23. Mai 2017  
13:00 Uhr**

**WSI, Seminarraum S 101**

## **“Towards telecom-band nanowire lasers on Si ”**

Abstract: Monolithic integration of III-V compound semiconductor lasers in the telecom band on Si still remains challenging. Nanowire structure provides an alternative solution because of its high ability of lattice relaxation. We have developed gold-free CMOS-compatible growth process for InP/InAs quantum nanostructure nanowires with high controllability (structure and doping) and superior optical property. The nanowire exhibits lasing behavior in the telecom band at room temperature.

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